PAP2617N

P-Ch -20V Fast Switching MOSFET

V_{DS}=-20V, I_D=-4.7A, $R_{DS(ON)}$=32mΩ

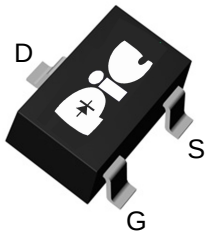
➢ General Description

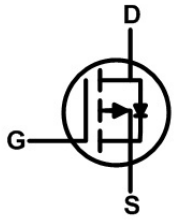
This PAP2617N P-Channel enhancement mode power field effect transistor is the high density trench technology and this advanced technology can provide excellent Rds(On) performance and efficiency for power switching and load switching application., this device also comply with the RoHS and Green Product requirement with full function reliability approved.

➢ Feature

●Super Low Gate Charge
●Green Device Available
●Excellent CdV/dt effect decline
●Advanced high cell density Trench technology
●SOT-23 Package design

➢ SOT-23





➢ Application

●Load Switch
●Small Power Switching
●Power Management

➢ Absolute Maximum Ratings

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	±12	V
Continuous Drain Current, V_{GS} @ -4.5V[1]	I_D@T_A=25℃	-4.7	A
Continuous Drain Current, V_{GS} @ -4.5V[1]	I_D@T_A=70℃	-3.8	A
Pulsed Drain Current[2]	I_{DM}	-18.8	A
Total Power Dissipation[3]	P_D@T_A=25℃	1	W
Storage Temperature Range	T_{STG}	-55 to 150	℃
Operating Junction Temperature Range	T_J	-55 to 150	℃
Thermal Resistance Junction-ambient [1]	$R_{\theta JA}$	125	℃/W
Thermal Resistance Junction-Case[1]	$R_{\theta JC}$	80	℃/W

➢ Electrical Characteristics (T_J=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V , I_D=-250uA	-20	---	---	V
BVDSS Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	Reference to 25℃ , I_D=-1mA	---	-0.01	---	V/℃
Static Drain-Source On-Resistance[2]	$R_{DS(ON)}$	V_{GS}=-4.5V , I_D=-4A	---	25	32	mΩ
		V_{GS}=-2.5V , I_D=-2A	---	32	40	
		V_{GS}=-1.8V , I_D=-1.5A		42	55	
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS}=V_{DS} , I_D =-250uA	-0.3	-0.5	-1.0	V
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}$		---	2.96	---	mV/℃
Drain-Source Leakage Current	I_{DSS}	V_{DS}=-16V , V_{GS}=0V , T_J=25℃	---	---	-1	uA
		V_{DS}=-16V , V_{GS}=0V , T_J=55℃	---	---	-5	
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±12V , V_{DS}=0V	---	---	±100	nA
Forward Transconductance	gfs	V_{DS}=-5V , I_D=-4A	---	21	---	S
Total Gate Charge (-4.5V)	Q_g	V_{DS}=-15V , V_{GS}=-4.5V , I_D=-4A	---	27.3	38.2	nC
Gate-Source Charge	Q_{gs}		---	3.6	5.0	
Gate-Drain Charge	Q_{gd}		---	6.5	9.1	
Turn-On Delay Time	$T_{d(on)}$	V_{DD}=-10V , V_{GS}=-4.5V , R_G=3.3Ω I_D=-4A	---	9.2	18.4	ns
Rise Time	T_r		---	59	106	
Turn-Off Delay Time	$T_{d(off)}$		---	99	198	
Fall Time	T_f		---	71	142	
Input Capacitance	C_{iss}	V_{DS}=-15V , V_{GS}=0V , f=1MHz	---	2280	3192	pF
Output Capacitance	C_{oss}		---	220	308	
Reverse Transfer Capacitance	C_{rss}		---	187	262	

➢ Diode Characteristics

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Continuous Source Current[1,4]	I_S	V_G=V_D=0V , Force Current	---	---	-4.7	A
Pulsed Source Current[2,4]	I_{SM}		---	---	-18.8	A
Diode Forward Voltage[2]	V_{SD}	V_{GS}=0V , I_S=-1A , T_J=25℃	---	---	-1	V
Reverse Recovery Time	t_{rr}	I_F=-4A , dI/dt=100A/μs , T_J=25℃	---	52	---	nS
Reverse Recovery Charge	Q_{rr}		---	28	---	nC

Note :

1.Pulse width limited by maximum junction temperature.

2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

3.Ensure that the channel temperature does not exceed 150°C.

4.The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

➢ Typical Characteristics

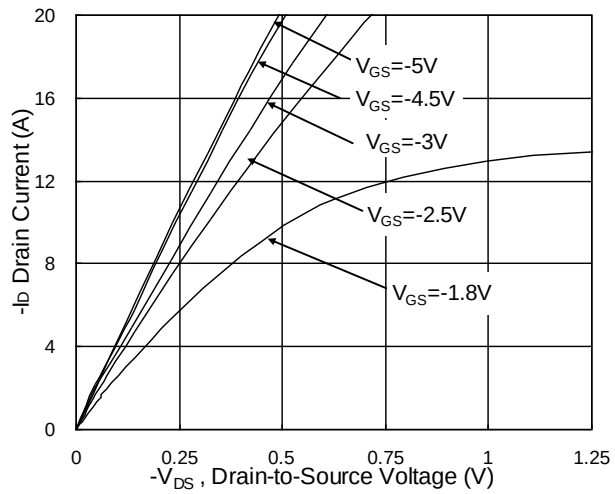


Fig.1 Typical Output Characteristics

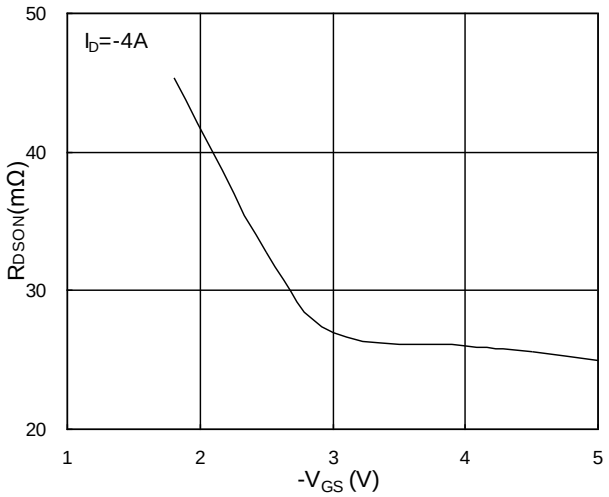


Fig.2 On-Resistance vs. Gate-Source

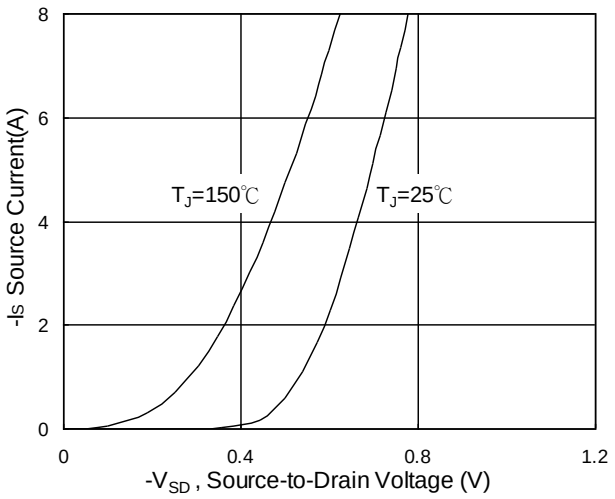


Fig.3 Forward Characteristics Of Reverse

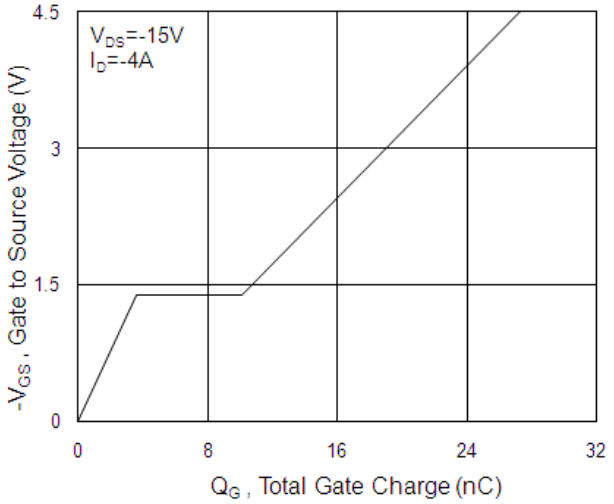


Fig.4 Gate-Charge Characteristics

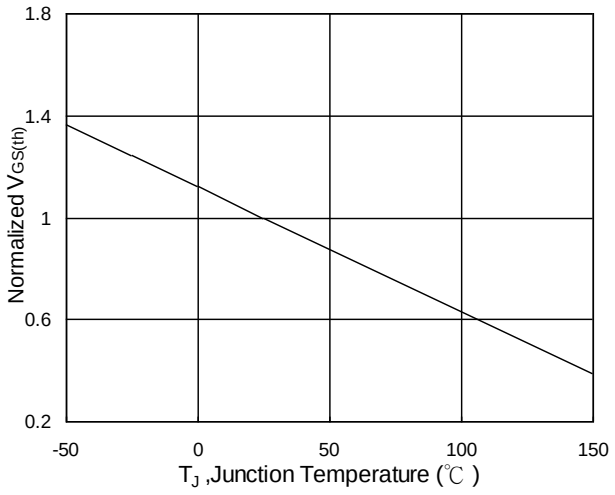


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

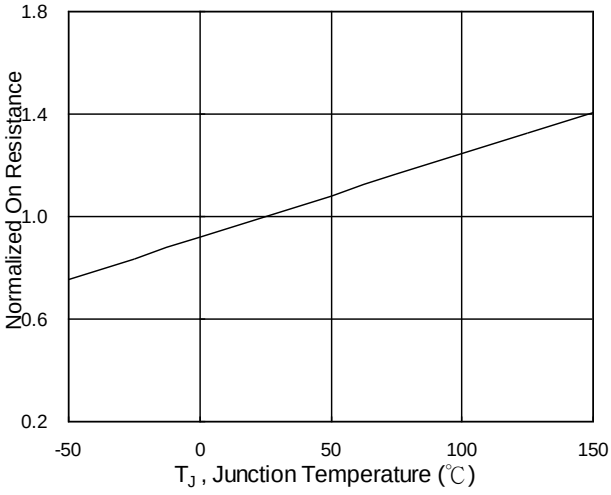


Fig.6 Normalized R_{DSON} vs. T_J

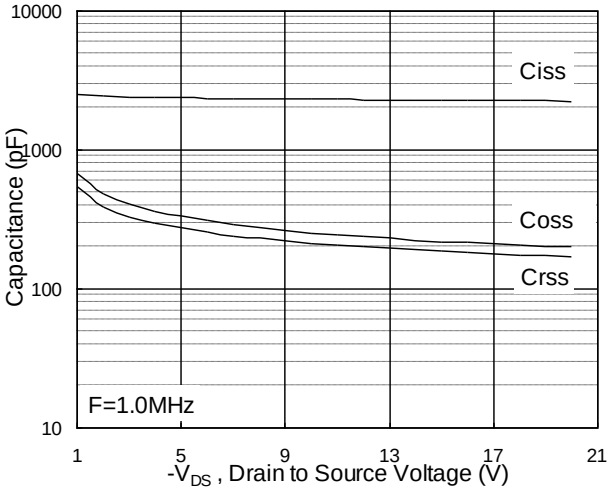


Fig.7 Capacitance

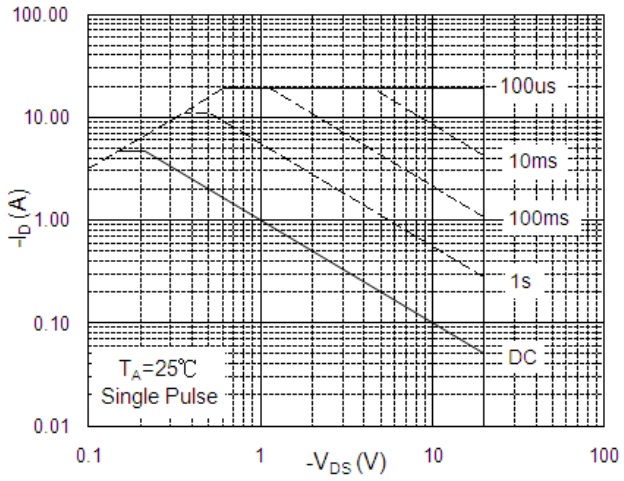


Fig.8 Safe Operating Area

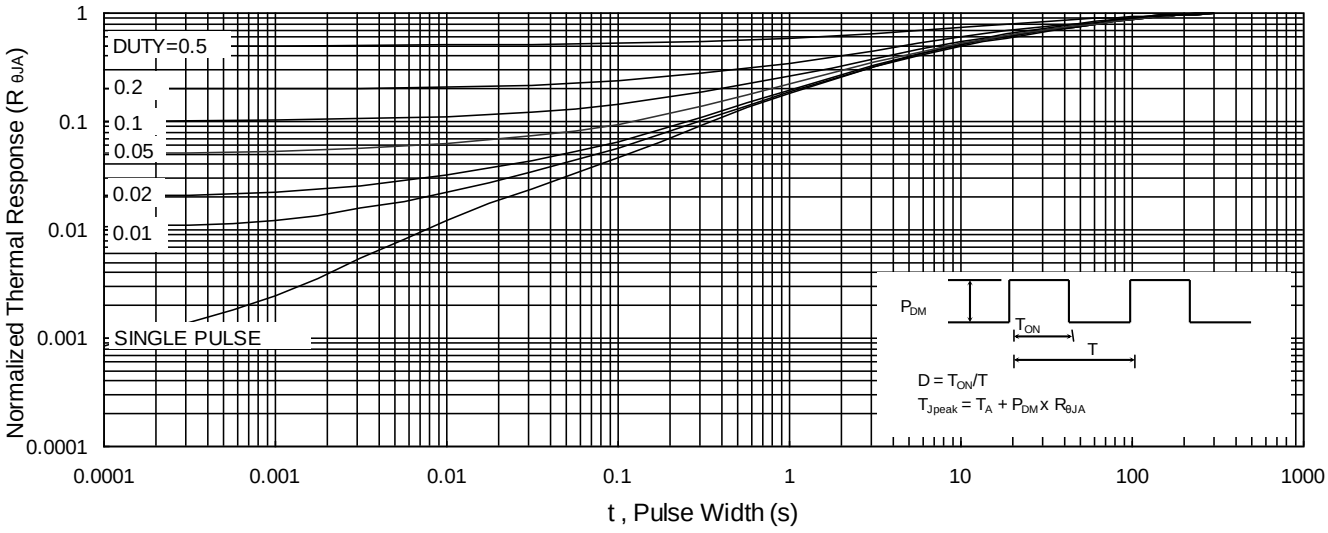


Fig.9 Normalized Maximum Transient Thermal Impedance

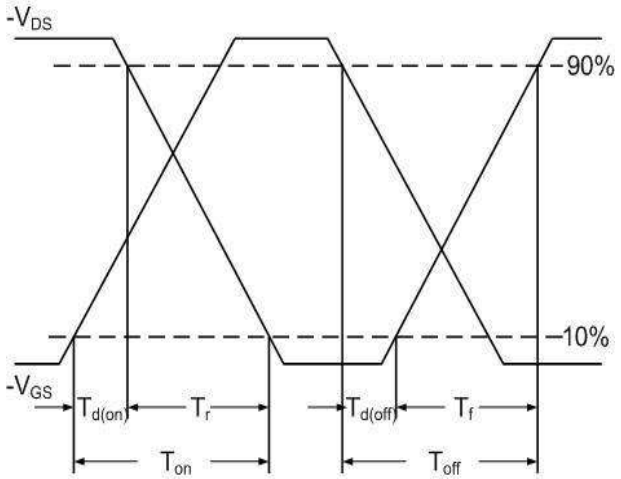


Fig.10 Switching Time Waveform

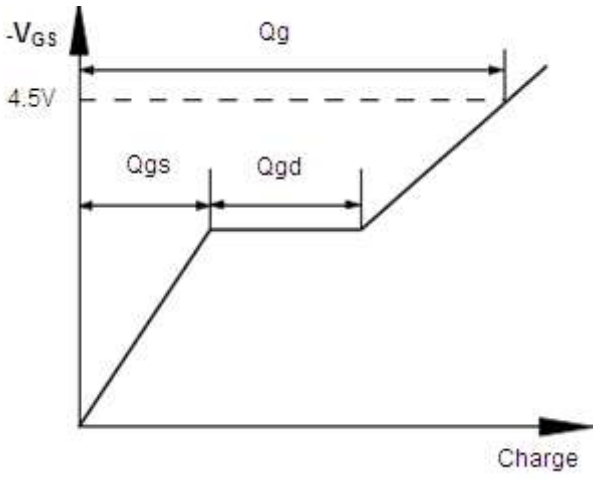
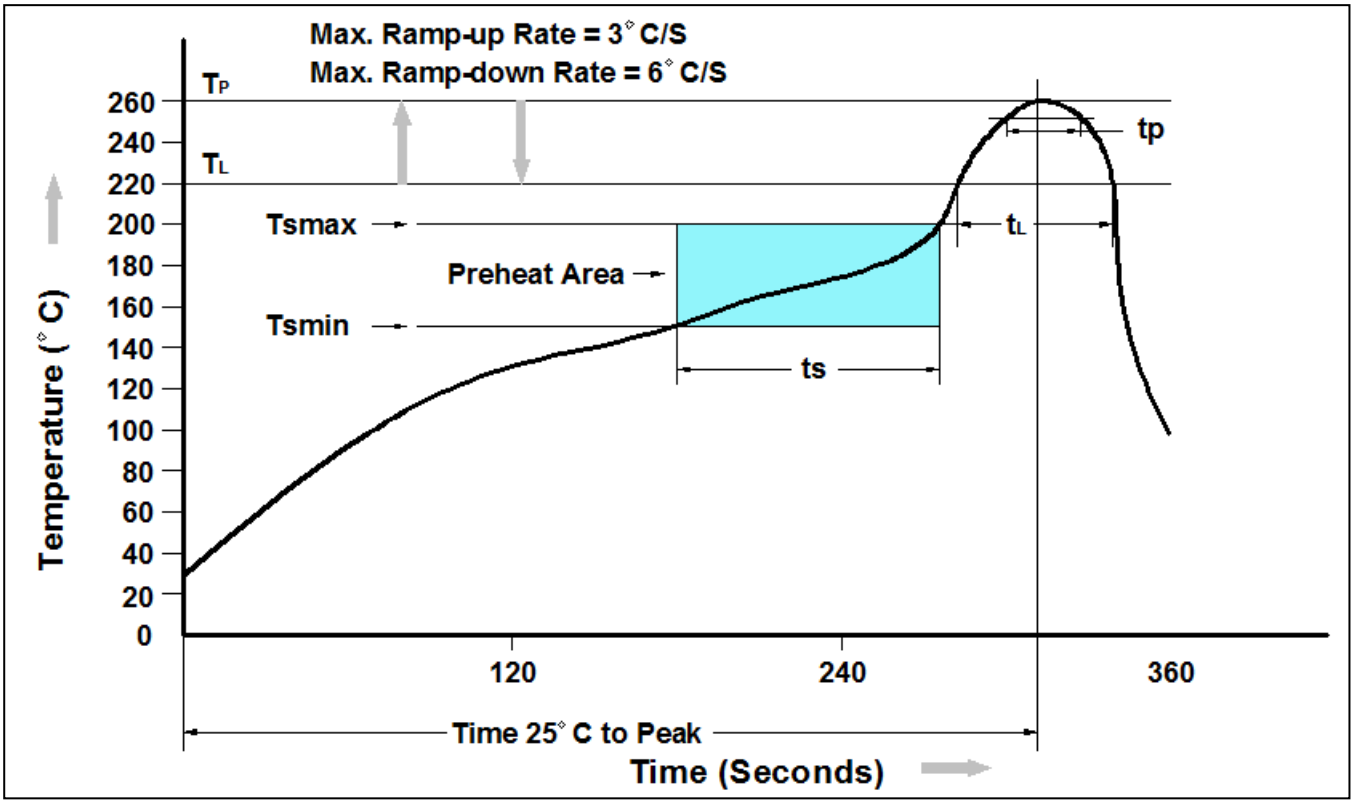


Fig.11 Gate Charge Waveform

➢ Recommand IR Reflow Soldering Thermal Profile

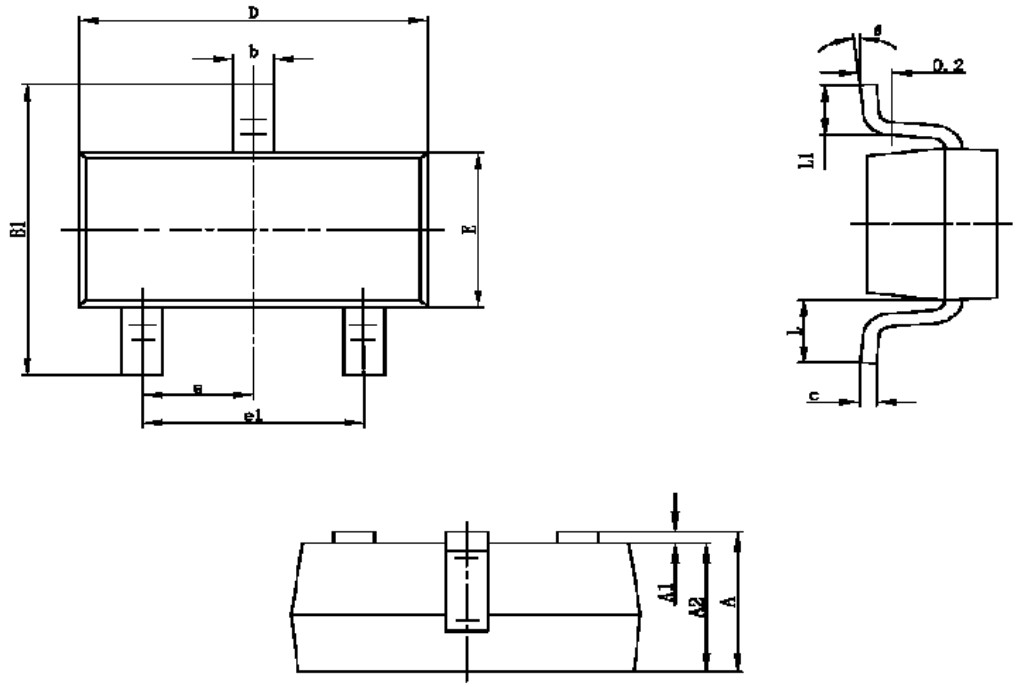


Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150°C
Temperature Max. (Tsmax)	200°C
Time (ts) from (Tsmin to Tsmax)	60-120 seconds
Average Ramp-up Rate (tL to tP)	3°C/second max.
Liquidous Temperature (TL)	217°C
Time (tL) Maintained Above (TL)	60 – 150 seconds
Peak Temperature	260°C +0°C / -5°C
Time (tP) within 5°C of actual Peak Temperature	30 seconds
Ramp-down Rate (TP to TL)	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.

➢ Ordering Information

Part Number	Description	Quantity
PAP2617N	SOT-23 Reel	3000 pcs

➢ Package Information (SOT- 23)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.400	0.012	0.016
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.700REF		0.028REF	
L1	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

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